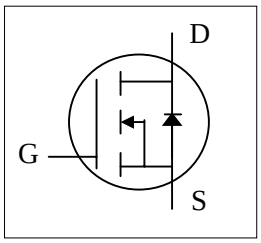
YGMOS Technology Co.,Ltd

GT50N10

N-CHANNEL ENHANCEMENT MODE POWER MOSFET

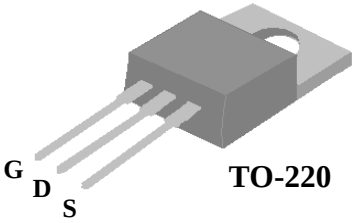
- ▼ **Simple Drive Requirement**
- ▼ **Lower Gate Charge**
- ▼ **Fast Switching Characteristic**
- ▼ **Halogen Free & RoHS Compliant Product**



BV_{DSS}	100V
$R_{DS(ON)}$	30mΩ
I_D	50A

Description

GT50N10 series are from YGMOS Power innovated design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.
The TO-220 package is widely preferred for all commercial-industrial through hole applications.
The low thermal resistance and low package cost contribute to the worldwide popular package.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Drain Current, V_{GS} @ 10V	50	A
I_D@T_C=100℃	Drain Current, V_{GS} @ 10V	40	A
I_{DM}	Pulsed Drain Current[1]	30	A
P_D@T_C=25℃	Total Power Dissipation	28	W
P_D@T_A=25℃	Total Power Dissipation	2	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Value	Units
Rthj-c	Maximum Thermal Resistance, Junction-case	4.5	℃/W
Rthj-a	Maximum Thermal Resistance, Junction-ambient	34	℃/W

Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250uA	100	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V, I_D=30A	-	25	30	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250uA	2	-	4	V
g_{fs}	Forward Transconductance	V_{DS}=10V, I_D=5A	-	5.6	-	S
I_{DSS}	Drain-Source Leakage Current	V_{DS}=80V, V_{GS}=0V	-	-	25	uA
I_{GSS}	Gate-Source Leakage	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA
Q_g	Total Gate Charge	I_D=5A	-	48	-	nC
Q_{gs}	Gate-Source Charge	V_{DS}=50V	-	13	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	V_{GS}=10V	-	10	-	nC
$t_{d(on)}$	Turn-on Delay Time	V_{DS}=20V	-	22	-	ns
t_r	Rise Time	I_D=5A	-	6	-	ns
$t_{d(off)}$	Turn-off Delay Time	R_G=1Ω	-	53	-	ns
t_f	Fall Time	V_{GS}=10V	-	12	-	ns
C_{iss}	Input Capacitance	V_{GS}=0V	-	3444	-	pF
C_{oss}	Output Capacitance	V_{DS}=10V	-	254	-	pF
C_{rss}	Reverse Transfer Capacitance	f=200KHZ	-	147	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage[2]	I_S=5A, V_{GS}=0V	-	-	1.3	V
t_{rr}	Reverse Recovery Time	I_S=5A, V_{GS}=0V	-	53	-	ns
Q_{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	130	-	nC

Notes:

1.Pulse width limited by Max. junction temperature.

2.Pulse test

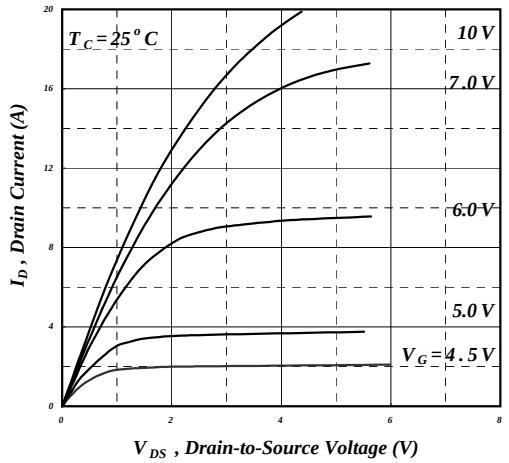


Fig 1. Typical Output Characteristics

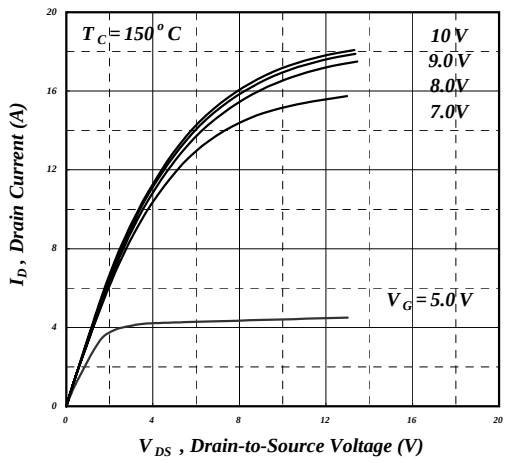


Fig 2. Typical Output Characteristics

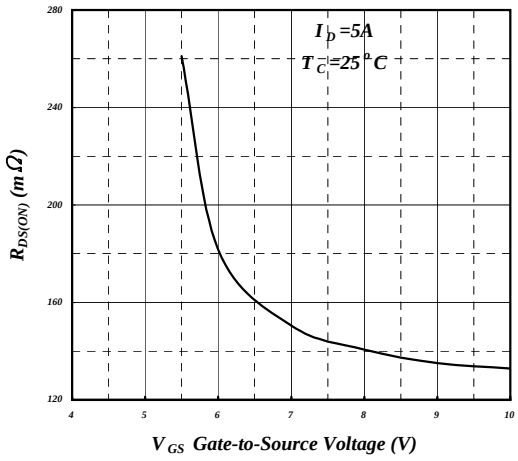


Fig 3. On-Resistance v.s. Gate Voltage

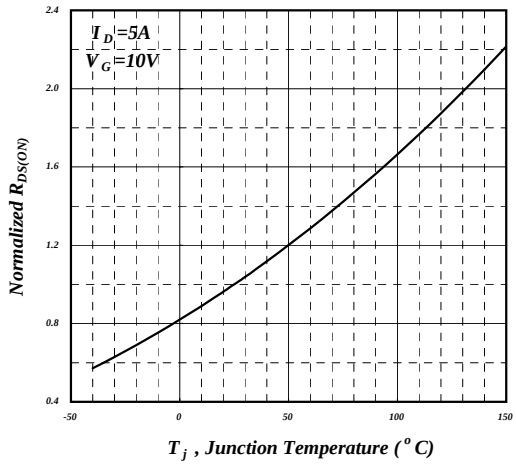


Fig 4. Normalized On-Resistance v.s. Junction Temperature

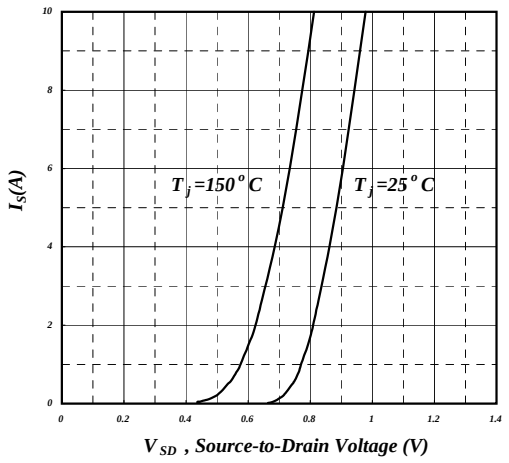


Fig 5. Forward Characteristic of Reverse Diode

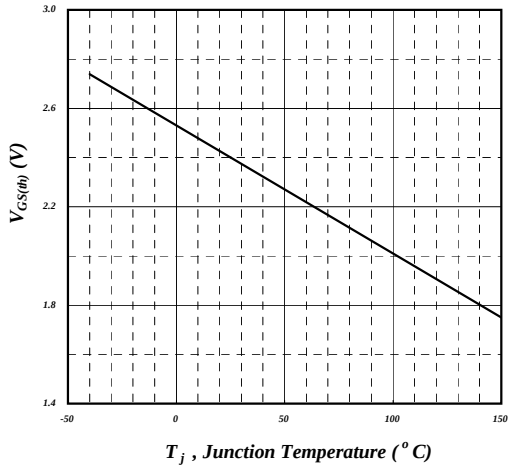


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

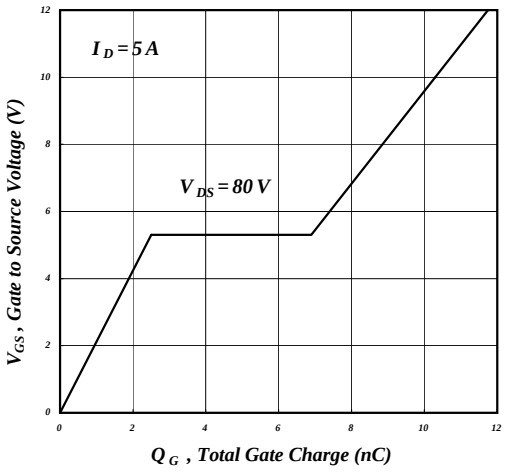


Fig 7. Gate Charge Characteristics

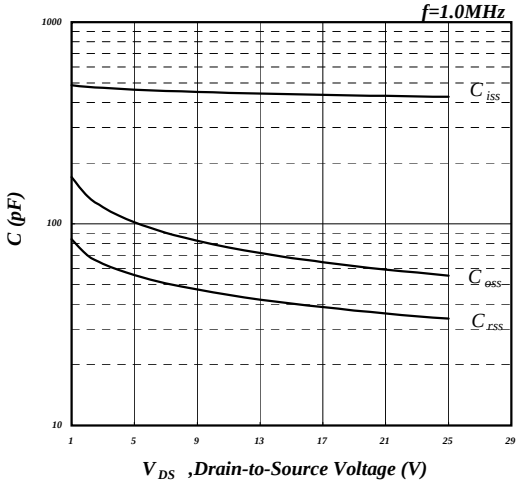


Fig 8. Typical Capacitance Characteristics

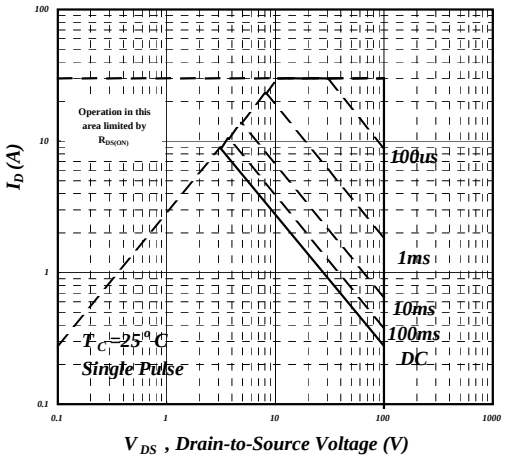


Fig 9. Maximum Safe Operating Area

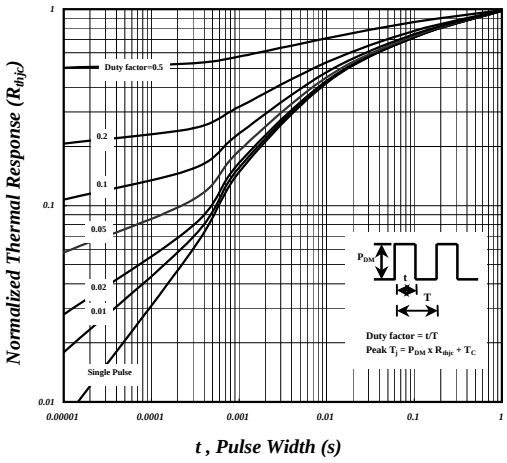


Fig 10. Effective Transient Thermal Impedance

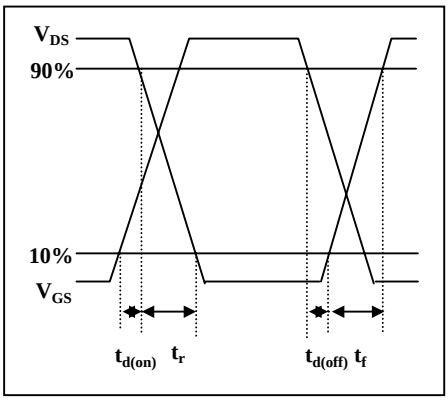


Fig 11. Switching Time Waveform

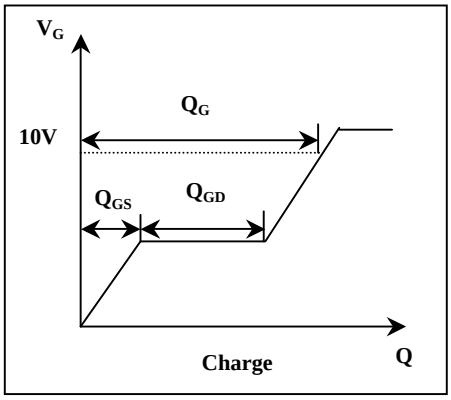


Fig 12. Gate Charge Waveform

MARKING INFORMATION